## NSN 5961-01-312-4663

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Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-312-4663 **Inclosure Material:** Ceramic **Overall Length:** 92.0 millimeters **Overall Height:** 20.0 millimeters Overall Width: 30.0 millimeters Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-240aa **Component Name And Quantity:** 2 semiconductor device thyristor **Mounting Method:** Press fit **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon all semiconductor device thyristor Voltage Rating In Volts Per Characteristic: 1300.0 nonrepetitive peak reverse voltage all semiconductor device thyristor and 1200.0 repetitive peak off-state voltage all semiconductor device thyristor and 1200.0 repetitive peak reverse voltage all semiconductor device thyristor **Current Rating Per Characteristic:** 60.00 amperes forward current, total rms universal all semiconductor device thyristor **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Special Features:** All semiconductor deivce thyristor junction pattern arrangement: pnpn **Terminal Type And Quantity:** 5 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:**